

Typical Applications

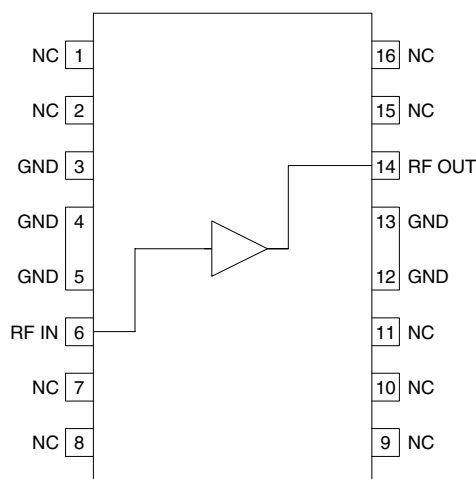
- CATV Distribution Amplifiers
- Cable Modems
- Broadband Gain Blocks
- Laser Diode Driver
- Return Channel Amplifier
- Base Stations

Product Description

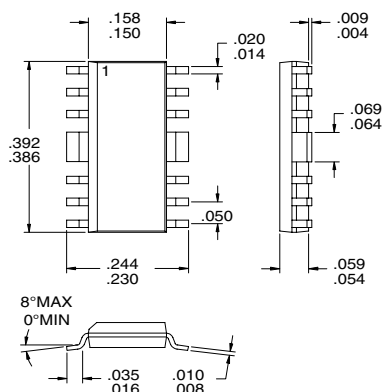
The RF2360 is a general purpose, low-cost, high-linearity RF amplifier IC. The device is manufactured on a Gallium Arsenide process and is featured in an SOP-16 batwing package. It has been designed for use as an easily cascadable 75Ω gain block with a Noise Figure of less than 2dB. Gain flatness better than 0.5dB from 5MHz to 1000MHz, and high linearity make this part ideal for cable TV applications. Other applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to 1000MHz. The device is self-contained with 75Ω input and output impedances providing less than 2:1 VSWR matching. For higher input and output return losses, see the evaluation schematic.

Optimum Technology Matching® Applied

- | | | |
|-------------------------------------|-----------------------------------|---|
| <input type="checkbox"/> Si BJT | <input type="checkbox"/> GaAs HBT | <input checked="" type="checkbox"/> GaAs MESFET |
| <input type="checkbox"/> Si Bi-CMOS | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si CMOS |



Functional Block Diagram



Package Style: SOP-16 BW

Features

- 5MHz to 1500MHz Operation
- Internally Matched Input and Output
- 20dB Small Signal Gain
- 1.2dB Noise Figure
- +24dBm Output Power
- Single 6V to 9V Positive Power Supply

Ordering Information

- | | |
|-------------|----------------------------------|
| RF2360 | Linear General Purpose Amplifier |
| RF2360 PCBA | Fully Assembled Evaluation Board |

RF Micro Devices, Inc.
7625 Thorndike Road
Greensboro, NC 27409, USA

Tel (336) 664 1233
Fax (336) 664 0454
<http://www.rfmd.com>

Absolute Maximum Ratings

Parameter	Rating	Unit
Device Current	175	mA
Device Voltage	9	V
Input RF Power	+10	dBm
Output Load VSWR	20:1	
Ambient Operating Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C



Caution! ESD sensitive device.

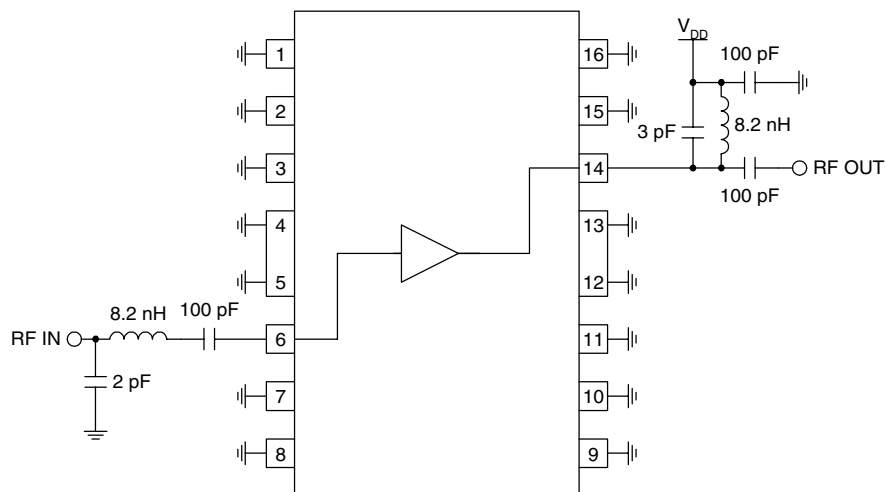
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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall (50Ω)					T=25 °C, V _{DD} =7V, 50Ω System, P _{IN} =-8dBm
Frequency Range		5 to 1500		MHz	3dB Bandwidth
Input VSWR		1.6:1			Appropriate values for the output DC blocking capacitor and bias inductor are required to maintain this VSWR over the intended operating frequency range.
Output VSWR		1.2:1			See note for Input VSWR.
Gain		20		dB	At 500MHz
Gain Flatness		+/-0.9		dB	5MHz to 1000MHz
Noise Figure		1.2		dB	At 500MHz
Noise Figure		1.5		dB	From 5MHz to 1000MHz
Output IP ₃		33.7		dBm	At 10MHz, Delta F1 and F2 = 1MHz
Output IP ₃		37.2		dBm	At 500MHz
Output IP ₃		36.4		dBm	At 1000MHz
Output IP ₂		46.3		dBm	At 100MHz, Delta F1 and F2 = 156MHz
Output IP ₂		44.4		dBm	At 1000MHz
Output P _{1dB}		21		dBm	At 10MHz
Output P _{1dB}		24		dBm	At 500MHz
Output P _{1dB}		23.7		dBm	At 1000MHz
Reverse Isolation		24		dB	At 500MHz
					T=25 °C, V _{DD} =9V, P _{IN} =-8dBm
Gain		20		dB	At 500MHz
Gain Flatness		+/-0.9		dB	5MHz to 1000MHz
Noise Figure		1.1		dB	At 500MHz
Noise Figure		1.5		dB	From 5MHz to 1000MHz,
Output IP ₃		34.8		dBm	At 10MHz, Delta F1 and F2 = 1MHz
Output IP ₃		38.1		dBm	At 500MHz
Output IP ₃		38.7		dBm	At 1000MHz
Output IP ₂		44.1		dBm	At 100MHz, Delta F1 and F2 = 156MHz
Output IP ₂		48.6		dBm	At 1000MHz
Output P _{1dB}		22.5		dBm	At 10MHz
Output P _{1dB}		25.1		dBm	At 500MHz
Output P _{1dB}		25.3		dBm	At 1000MHz
Power Supply					
Supply Voltage (V _{DD})	6	7	9	V	
Operating Current Range	100	104	109	mA	

Pin	Function	Description	Interface Schematic
1	NC	No connection. This pin should be connected to the ground plane.	
2	NC	Same as pin 1.	
3	GND	Ground connection. Keep traces physically short and connect immediately to ground plane for best performance. Each ground pin should have a via to the ground plane.	
4	GND	Same as pin 3.	
5	GND	Same as pin 3.	
6	RF IN	RF input pin. This pin is internally DC blocked. An external DC blocking capacitor is not required.	
7	NC	Same as pin 1.	
8	NC	Same as pin 1.	
9	NC	Same as pin 1.	
10	NC	Same as pin 1.	
11	NC	Same as pin 1.	
12	GND	Same as pin 3.	
13	GND	Same as pin 3.	
14	RF OUT	RF output and bias pin. Because DC is present on this pin, a DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. For biasing, only an RF choke is needed.	
15	NC	Same as pin 1.	
16	NC	Same as pin 1.	

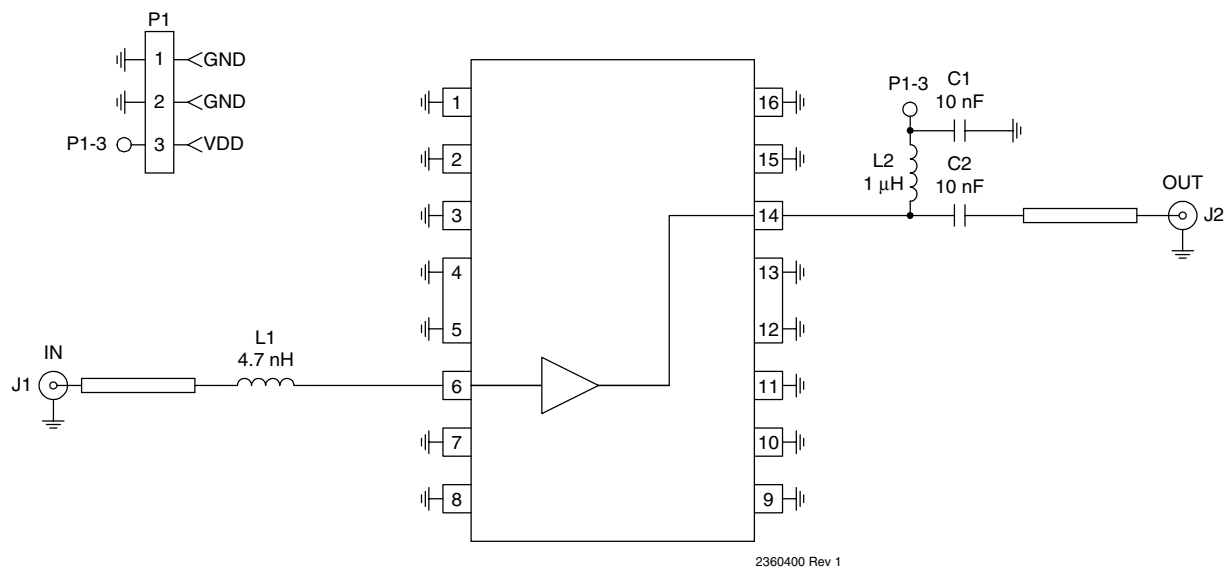
Application Schematic

869-894MHz Narrowband Operation

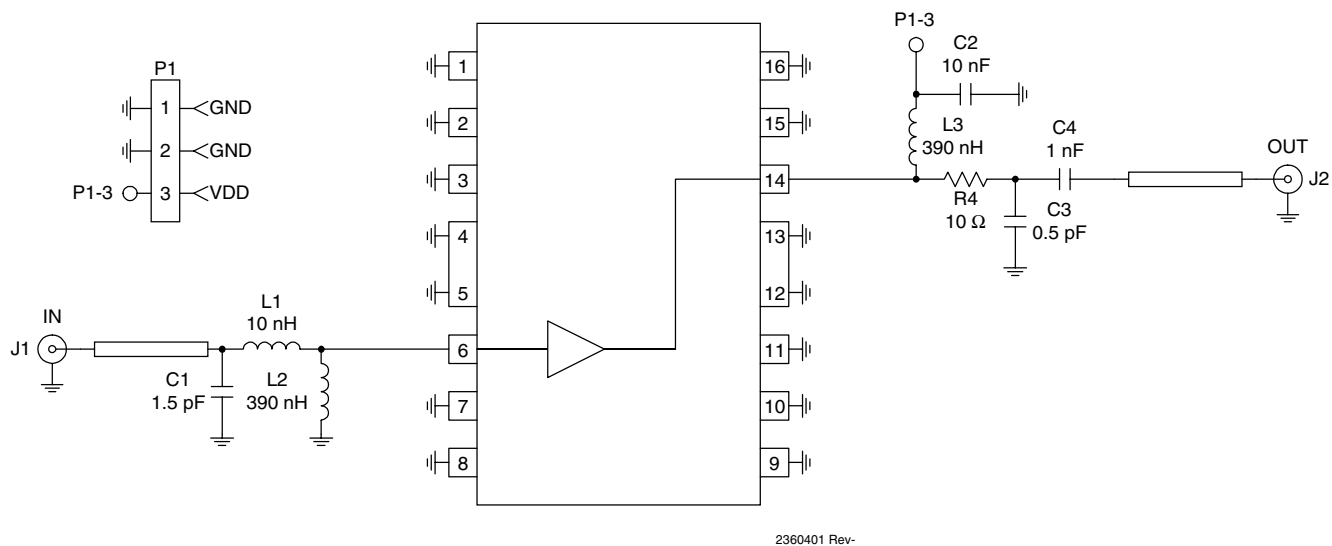


Evaluation Board Schematic - 50Ω

(Download [Bill of Materials](http://www.rfmd.com) from www.rfmd.com.)

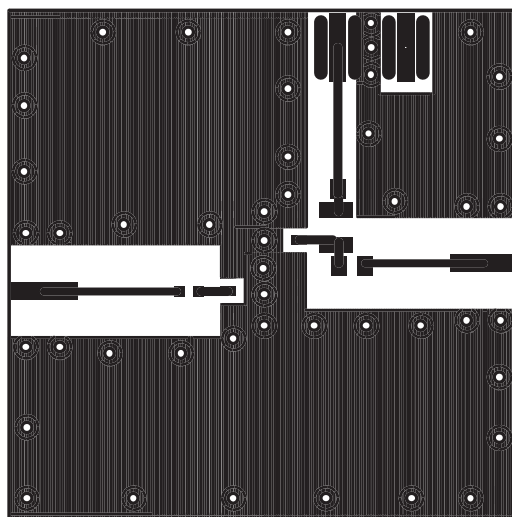
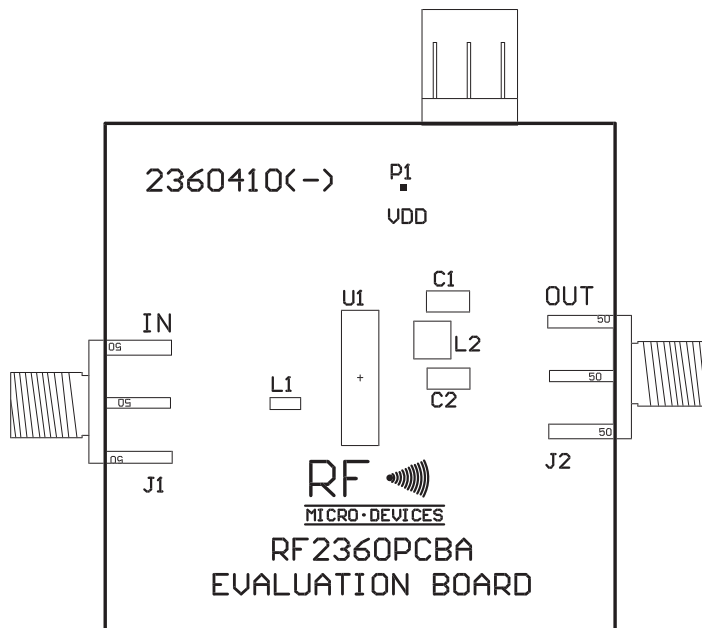


Evaluation Board Schematic - 75Ω



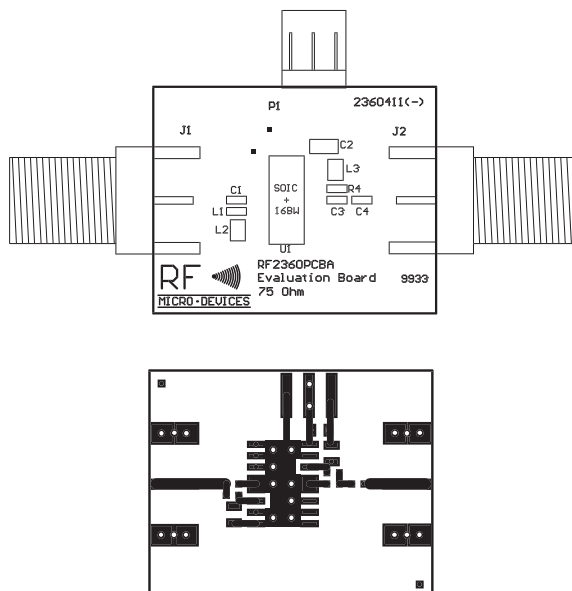
Evaluation Board Layout - 50 Ω Board Size 1.5" x 1.5"

Board Thickness 0.031", Board Material FR-4

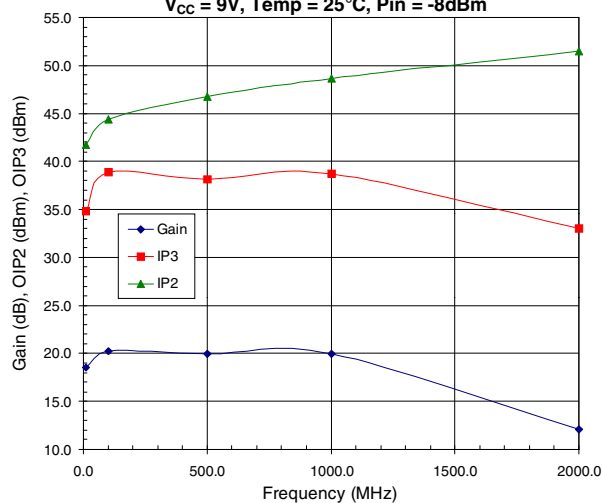


Evaluation Board Layout - 75Ω

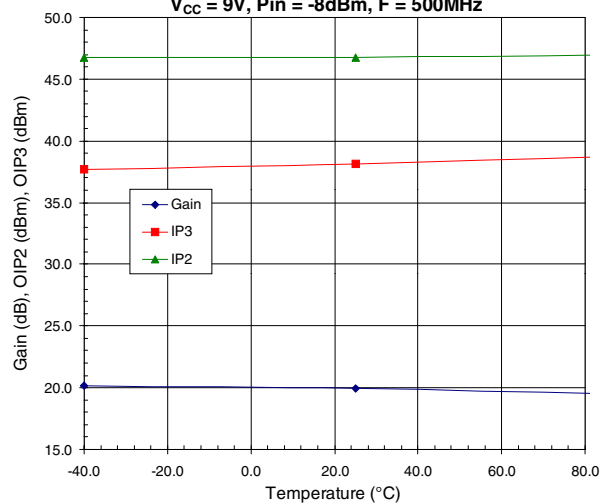
Board Thickness 0.062", Board Material FR-4



Gain, OIP2 and OIP3 versus Frequency

 $V_{CC} = 9V$, Temp = 25°C, Pin = -8dBm

Gain, OIP2 and OIP3 versus Temperature

 $V_{CC} = 9V$, Pin = -8dBm, F = 500MHz

Gain, OIP2 and OIP3 versus Pin

 $V_{CC} = 9V$, Temp = 25°C, F = 500MHz